



### 30V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>C</sub> = +25°C
30V	$2.2m\Omega$ @ $V_{GS} = 10V$	170A
	$3.2 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	140A

## **Description and Applications**

PowerDI5060-8

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- **Engine Management Systems**
- **Body Control Electronics**
- **DC-DC Converters**

### **Features**

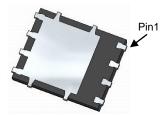
- Rated to +175°C -Ideal for High Ambient Temperature **Environments**
- 100% Unclamped Inductive Switching (Test in Production) -Ensures More Reliable and Robust End Application
- <1.1mm Package Profile Ideal for Thin Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

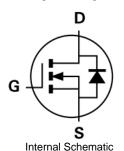
- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (93)
- Weight: 0.097 grams (Approximate)

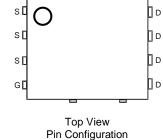






**Bottom View** 





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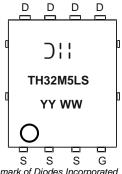
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH32M5LPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

#### **Marking Information**



⊃¦¦ = Manufacturer's Marking TH32M5LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated DMTH32M5LPSQ

Document number: DS40687 Rev. 3 - 2



# **Maximum Ratings** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	30	V		
Gate-Source Voltage	$V_{GSS}$	±16	V		
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 7)	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	170 120	Α
Maximum Continuous Body Diode Forward Current (Note	I <sub>S</sub>	80	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	350	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	350	Α
Avalanche Current, L = 0.1mH			I <sub>AS</sub>	50	Α
Avalanche Energy, L = 0.1mH			Eas	140	mJ

## Thermal Characteristics (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	$P_{D}$	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	54	°C/W	
Total Power Dissipation (Note 7) $T_C = +25^{\circ}C$		$P_{D}$	100	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.5	°C/W
Operating and Storage Temperature Range		$T_{J_{I}}T_{STG}$	-55 to +175	°C

# **Electrical Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

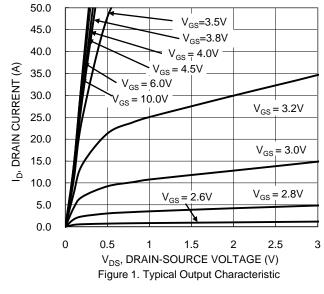
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	Syllibol	IVIIII	тур	IVIAX	Offic	rest Condition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	1000		I			100 =111, 100 11	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1		3	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$	
Chatia Duain Course On Besistance		_	1.6	2.2	0	$V_{GS} = 10V, I_D = 30A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	2.6	3.2	mΩ	$V_{GS} = 4.5V, I_D = 30A$	
Diode Forward Voltage	$V_{SD}$	_	0.8	1.1	V	$V_{GS} = 0V, I_{S} = 30A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	3944	_		V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	1267	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	186	_			
Gate Resistance	$R_g$	_	0.6	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	_	34	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	68	_	nC	\/ 45\/ L 20A	
Gate-Source Charge	$Q_{gs}$	_	8	_	nC	$V_{DS} = 15V, I_{D} = 20A$	
Gate-Drain Charge	Q <sub>qd</sub>	_	15	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7.2	_			
Turn-On Rise Time	t <sub>R</sub>	_	13.2	_		$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	37.5	_	ns	$I_D = 15A$ , $R_g = 3\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	23.9	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	28.7	_	ns	1 45A di/dt 500A/uc	
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	45.8		nC	$I_S = 15A$ , di/dt = 500A/ $\mu$ s	

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad). 8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to production testing.





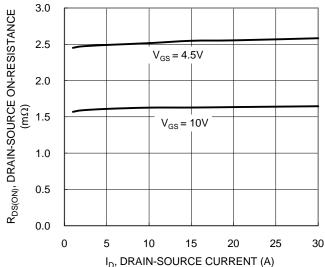


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

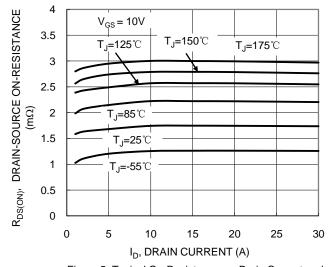
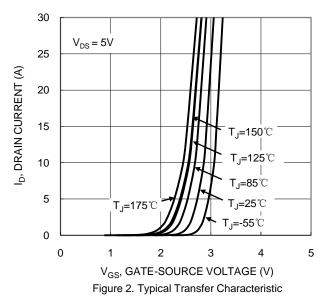
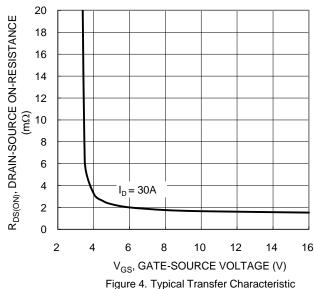


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





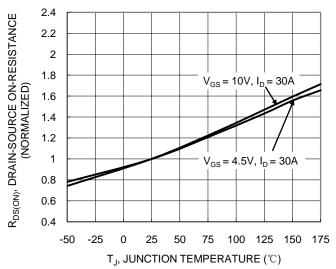


Figure 6. On-Resistance Variation with Temperature



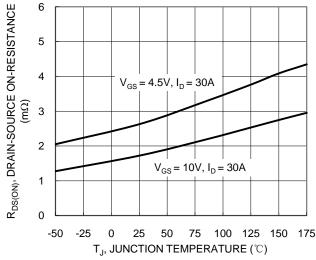


Figure 7. On-Resistance Variation with Temperature

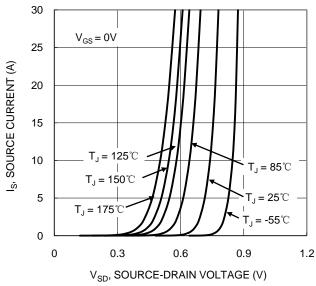


Figure 9. Diode Forward Voltage vs. Current

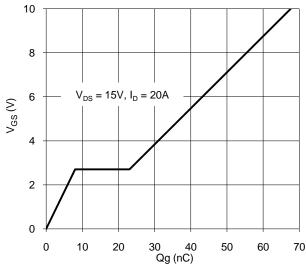


Figure 11. Gate Charge

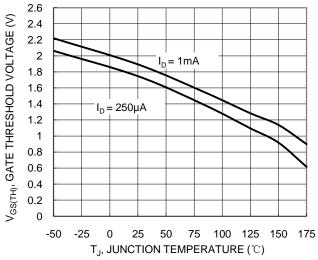


Figure 8. Gate Threshold Variation vs. Junction Temperature

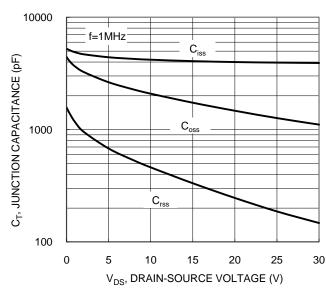
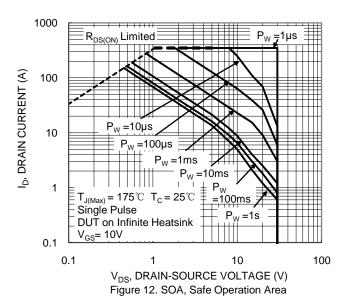


Figure 10. Typical Junction Capacitance





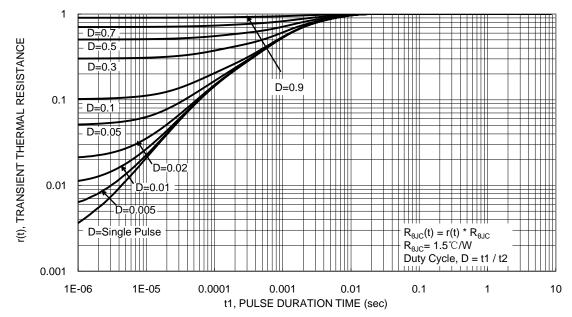


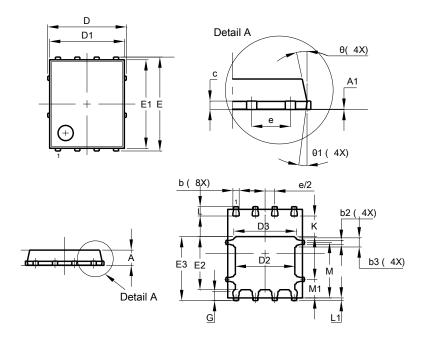
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

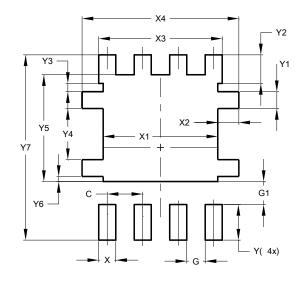


PowerDI5060-8					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70 4.10 3.90				
D3	3.90 4.30 4.10				
Е	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC	;		
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51 0.71 0.6		0.61		
L1	0.100 0.200 0.17		0.175		
M	3.235 4.035 3.6		3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All	All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

**April 2018** 



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